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FSB50825AS Motion SPM[®] 5 系列

2019年9月

特性

- 通过 UL 第 E209204 号认证 (UL1557)
- 500 V $R_{DS(on)}$ = 0.45 Ω (最大值)FRFET MOSFET 三相逆变器,带有栅极驱动器和保护功能
- 内置自举二极管以简化印刷电路板布局
- 低端 MOSFET 的三个独立开源引脚用于三相电流感测
- 高电平有效接口,可用于 3.3 / 5 V 逻辑电平, 施密特触 发脉冲输入
- 针对低电磁干扰进行优化
- 内置于 HVIC 的温度感测
- 用于栅极驱动和欠压保护的 HVIC
- 绝缘等级: 1500 V_{rms} / 分钟
- 湿度敏感等级 (MSL) 3
- 符合 RoHS 标准

应用

• 小功率交流电机驱动器的三相逆变器驱动

相关资料

- <u>RD-FSB50450A Reference Design for Motion SPM 5</u> <u>Series Ver.2</u>
- AN-9082 Motion SPM5 Series Thermal Performance by Contact Pressure
- AN-9080 User's Guide for Motion SPM 5 Series V2

概述

FSB50825AS 是一款先进的 Motion SPM[®] 5 模块,为交流感应、无刷直流电机和 PMSM 电机提供非常全面的高性能逆变器 输出平台。这些模块综合优化了内置 MOSFETs(FRFET®技术)的栅极驱动以最小化电磁干扰和能量损耗。同时也提供多重模组保护特性,集成欠压闭锁和热量监测。内置的高速 HVIC 只需要一个单电源电压,将逻辑电平栅极输入转化为适合驱动模块内部 MOSFET 的高电压,高电流驱动信号。独立的开源 MOSFET 端子在每个相位均有效,可支持大量不同种类的控制算法。



封装标识与定购信息

器件标识	器件	封装	卷尺寸	包装类型	数量
FSB50825AS	FSB50825AS	SPM5Q-023	330 mm	卷带和卷盘	450

绝对最大额定值

逆变器部分 (单个 MOSFET,除非另有说明。)

符号	参数	工作条件	额定值	单位
V_{DSS}	单个 MOSFET 的漏极 - 源极电压		250	V
*I _{D 25}	单个 MOSFET 的漏极持续电流	T _C = 25°C	3.6	Α
*I _{D 80}	单个 MOSFET 的漏极持续电流	T _C = 80°C	2.7	Α
*I _{DP}	单个 MOSFET 的漏极峰值电流	T _C = 25°C, PW < 100 μs	9.0	Α
*I _{DRMS}	单个 MOSFET 的漏极电流有效值	$T_C = 80$ °C, $F_{PWM} < 20 \text{ kHz}$	1.9	A _{rms}
*P _D	最大功耗	T _C = 25°C, 单个 MOSFET	14.2	W

控制部分 (单个 HVIC,除非另有说明。)

符号	参数	工作条件	额定值	单位
V _{CC}	控制电源电压	施加在 V _{CC} 和 COM 之间	20	V
V_{BS}	高端偏压	施加在 V _B 和 V _S 之间	20	V
V _{IN}	输入信号电压	施加在 V _{IN} 和 COM 之间	$-0.3 \sim V_{CC} + 0.3$	V

自举二极管部分 (单个自举二极管,除非另有说明。)

符号	参数	工作条件	额定值	单位
V_{RRMB}	最大重复反向电压		250	V
* I _{FB}	正向电流	T _C = 25°C	0.5	Α
* I _{FPB}	正向电流 (峰值)	T _C = 25°C,脉冲宽度小于 1 ms	1.5	Α

热阻

符号	参数	工作条件	额定值	单位
$R_{ heta JC}$	结点 - 壳体的热阻	逆变器工作条件下的单个 MOSFET (注 1)	8.8	°C/W

整个系统

符号	参数	工作条件	额定值	单位
T_J	工作结温		-40 ~ 150	°C
T _{STG}	存储温度		-40 ~ 125	°C
V _{ISO}	绝缘电压	60 Hz,正弦波形, 1 分钟,连接陶 瓷基板到引脚	1500	V_{rms}

注:

- 1. 关于壳体温度 (T_C)的测量点,参见图 4。
- 2. 标记为"*"的为计算值或设计因素。

引脚描述

引脚号	引脚名	引脚描述
1	COM	IC 公共电源接地
2	V _{B(U)}	U 相高端 MOSFET 驱动的偏压
3	V _{CC(U)}	U相IC和低端 MOSFET 驱动的偏压
4	IN _(UH)	U 相高端的信号输入
5	IN _(UL)	U 相低端的信号输入
6	N.C	无连接
7	V _{B(V)}	V 相高端 MOSFET 驱动的偏压
8	V _{CC(V)}	V相IC和低端 MOSFET 驱动的偏压
9	IN _(VH)	V 相高端的信号输入
10	IN _(VL)	V 相低端的信号输入
11	V _{TS}	HVIC 温度感测输出
12	V _{B(W)}	W 相高端 MOSFET 驱动的偏压
13	V _{CC(W)}	W 相 IC 和低端 MOSFET 驱动的偏压
14	IN _(WH)	W 相高端的信号输入
15	IN _(WL)	W 相低端的信号输入
16	N.C	无连接
17	Р	直流输入正端
18	U, V _{S(U)}	高端 MOSFET 驱动的 U 相偏压接地输出
19	N _U	U 相的直流输入负端
20	N _V	V 相的直流输入负端
21	V, V _{S(V)}	高端 MOSFET 驱动的 V 相偏压接地输出
22	N _W	W 相的直流输入负端
23	W, V _{S(W)}	高端 MOSFET 驱动的 W 相偏压接地输出

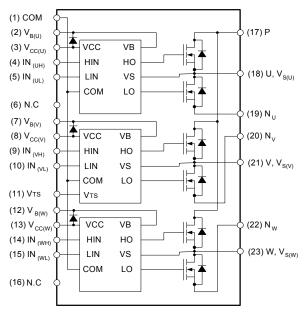


图 1. 引脚布局和内部框图 (仰视图)

注:

3. 每个低端 MOSFET 的源极端子与 Motion SPM^{\otimes} 5 中的电源接地或偏压接地不连接。外部连接应当如图 3 所示。

电气特性 $(TJ = 25^{\circ}C, V_{CC} = V_{BS} = 15 \text{ V}, 除非另有说明。)$

逆变器部分 (单个 MOSFET,除非另有说明。)

符号	参数	工作条件	最小值	典型值	最大值	单位
BV _{DSS}	漏极一源极击穿电压	$V_{IN} = 0 \text{ V}, I_D = 1 \text{ mA} (\ge 1)$	250	-	-	V
I _{DSS}	零栅极电压漏极电流	V _{IN} = 0 V, V _{DS} = 250 V	-	-	1	mA
R _{DS(on)}	漏极至源极静态导通 电阻	$V_{CC} = V_{BS} = 15 \text{ V}, V_{IN} = 5 \text{ V}, I_D = 2.0 \text{ A}$	-	0.33	0.45	Ω
V _{SD}	漏极一源极二极管正向 电压	$V_{CC} = V_{BS} = 15 \text{ V}, V_{IN} = 0 \text{ V}, I_D = -2.0 \text{ A}$	-	-	1.2	٧
t _{ON}		V _{PN} = 150 V, V _{CC} = V _{BS} = 15 V, I _D = 2.0 A	-	950	-	ns
t _{OFF}			-	520	-	ns
t _{rr}	开关时间	V _{IN} = 0 V ↔ 5 V, 电感负载 L = 3 mH 高端和低端 MOSFET 开关	-	150	-	ns
E _{ON}		(注 2)	-	100	-	μJ
E _{OFF}			-	10	-	μJ
RBSOA	反向偏压安全工作区	V_{PN} = 200 V, V_{CC} = V_{BS} = 15 V, I_{D} = I_{DP} , V_{DS} = BV_{DSS} , T_{J} = 150°C 高端和低端 MOSFET 开关(注 3)		整个[⊠域	

控制部分 (单个 HVIC, 除非另有说明。)

符号	参数		工作条件		典型值	最大值	单位
I _{QCC}	V _{CC} 静态电流	V _{CC} = 15 V, V _{IN} = 0 V	施加在 V _{CC} 和 COM 之间	-	ı	200	μΑ
I_{QBS}	V _{BS} 静态电流	V _{BS} = 15 V, V _{IN} = 0 V	施加在 V _{B(U)} - U, V _{B(V)} - V, V _{B(W)} - W	-	-	100	μΑ
UV _{CCD}	你带有压但拉(图 0)	V _{CC} 欠压保护检	V _{CC} 欠压保护检测电平		8.0	9.4	٧
UV _{CCR}	低端欠压保护 (图 8)	V _{CC} 欠压保护复位电平		8.0	8.9	9.8	>
UV_{BSD}	高端欠压保护 (图 9)	V _{BS} 欠压保护检验	测电平	7.4	8.0	9.4	>
UV_BSR		V _{BS} 欠压保护复	位电平	8.0	8.9	9.8	>
V_{TS}	HVIC 温度感测电压输出	V _{CC} = 15 V, T _{HVIC} = 25°C (注 4)		600	790	980	mV
V _{IH}	导通阈值电压	逻辑高电平		-	-	2.9	V
V _{IL}	关断阈值电压	逻辑低电平	施加在 V _{IN} 和 COM 之间	0.8	-	-	V

自举二极管部分 (单个自举二极管,除非另有说明。)

符号	参数	工作条件	最小值	典型值	最大值	单位
V_{FB}	正向电压	I _F = 0.1 A, T _C = 25°C (注 5)	ı	2.5	ı	V
t _{rrB}	反向恢复时间	$I_F = 0.1 \text{ A}, T_C = 25^{\circ}\text{C}$	ı	80	ı	ns

注:

- 1. BV_{DSS} 是 Motion SPM[®] 5 产品中的单个 MOSFET 的漏极和源极端子之间的绝对最大额定电压。考虑到寄生电感,V_{PN} 应远低于该值,因此 V_{PN} 在任何情况下不得超过 BV_{DSS}。
- 2. t_{ON} 和 t_{OFF} 包括内部驱动 IC 的传输延迟。所列出的数值是在实验室测试条件下测得,在实际应用中因为印刷电路板和布线的差异,数值也会有所不同。请参阅图 6 介绍的开关时间定义,以及图 7 中的开关测试电路。
- 3. 每个 MOSFET 在开关工作时的峰值电流和电压也应在安全工作区 (SOA) 的范围内。请参阅图 7 中的 RBSOA 测试电路,它与开关测试电路相同。
- 4. Vts 只能用作模块的温度感测,但不能自动关闭 MOSFETs
- 5. 内置自举二极管其阻抗特性约为 15 Ω。请参阅图 2。

推荐工作条件

符号	参数	工作条件	最小值	典型值	最大值	单位
V_{PN}	电源电压	施加在P和N之间	-	150	200	V
V _{CC}	控制电源电压	施加在 V _{CC} 和 COM 之间	13.5	15.0	16.5	V
V_{BS}	高端偏压	施加在 V _B 和 V _S 之间	13.5	15.0	16.5	V
V _{IN(ON)}	输入导通阈值电压	** TO COM > CO	3.0	-	V _{CC}	V
V _{IN(OFF)}	输入关断阈值电压	施加在 V _{IN} 和 COM 之间	0	-	0.6	V
t _{dead}	防止桥臂直通的死区时间	$V_{CC} = V_{BS} = 13.5 \sim 16.5 \text{ V}, T_{J} \le 150^{\circ}\text{C}$	1.0	-	-	μs
f_{PWM}	PWM 开关频率	$T_{\rm J} \leq 150^{\circ}{\rm C}$	-	15	-	kHz

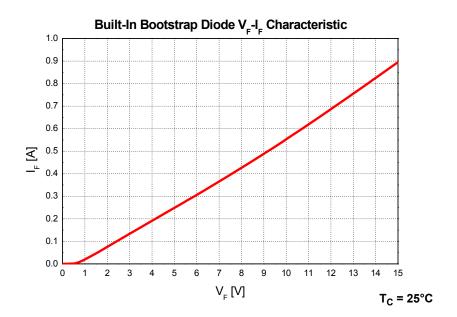


图 2. 内置自举二极管特性 (典型值)

These values depend on PWM control algorithm

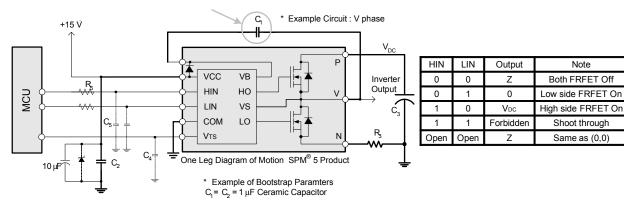


图 3. 推荐的 MCU 接口和自举电路及其参数

注:

- 1. 自举电路的参数取决于 PWM 算法。上述为开关频率为 15 kHz 时的参数的典型例子。
- 2. Motion SPM 5 产品和 MCU (虚线显示部分)的每个输入端的 RC 耦合 (R_5 和 C_5)和 C_4 ,可用于防止由浪涌噪声产生的错误信号。
- 3. 印刷电路板图形中的粗线应尽量短且粗,以减少电路中的寄生电感,从而导致浪涌电压的降低。旁路电容 C_1 , C_2 和 C_3 应具有良好的高频特性,以吸收高频纹波电流。

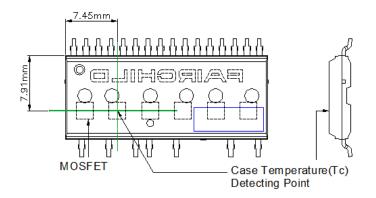


图 4. 壳体温度测量

注:

4. 将热电耦贴在 SPM 5 封装 (如果应用到,放在 SPM 5 封装和散热片中间)的散热片的顶部,以获得正确的温度测量数值。

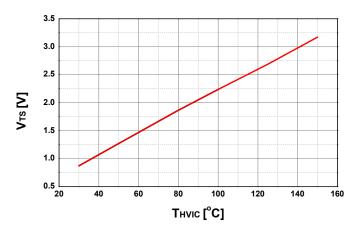


图 5. V_{TS} 的温度曲线 (典型值)

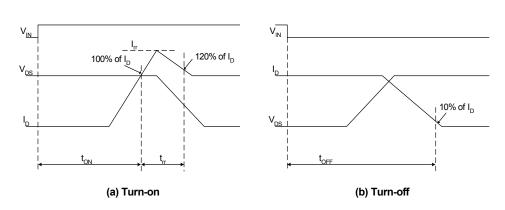


图 6. 开关时间定义

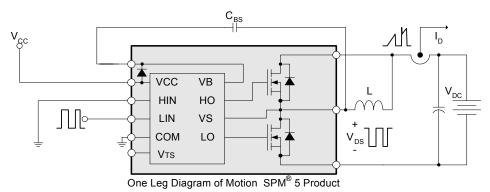
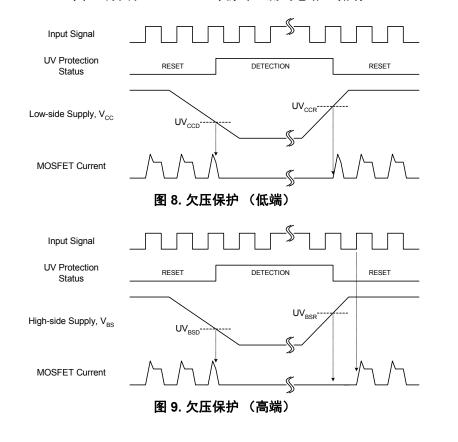


图 7. 开关和 RBSOA (单脉冲)测试电路 (低端)



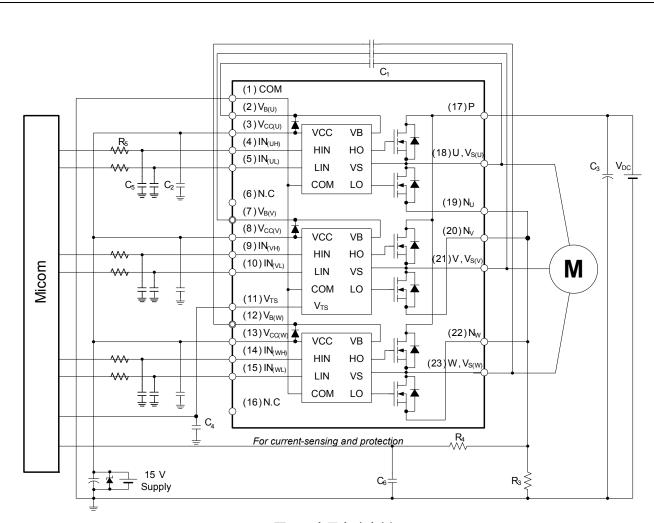
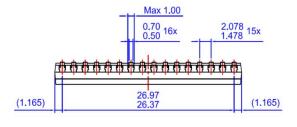


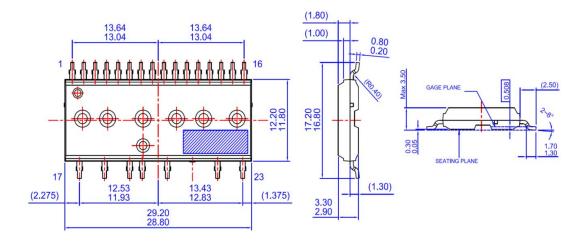
图 10. 应用电路实例

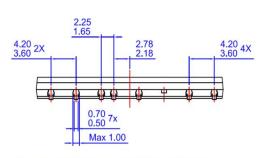
注:

- 1. 关于引脚的位置,请参阅图 1。
- 2. Motion SPM $^{\otimes}$ 5 产品和 MCU 的每个输入端的 RC 耦合 (R $_{5}$ 和 C $_{5}$, R $_{4}$ 和 C $_{6}$) 和 C $_{4}$,能有效的防止由浪涌噪声产生的错误的输入信号。
- 3. 由于位于 COM 和低端 MOSFET 的源极端子之间, R_3 的压降会影响低端的开关性能和自举特性。为此,稳态情况下 R_3 的压降应小于 $1\,$ V 。
- 4. 为避免浪涌电压和 HVIC 故障,接地线和输出端子之间的接线应短且粗。
- 5. 所有的滤波电容器应紧密连接到 Motion SPM 5 产品,它们应当具有能够很好的阻挡高频纹波电流的特性。

封装轮廓详图







3.90 2X 17 1.95 2.475

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Datasheet Identification	Product Status	Definition
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Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
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